

General Description

SFGMOS[®] MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially optimized for high systems with gate driving voltage greater than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery



Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

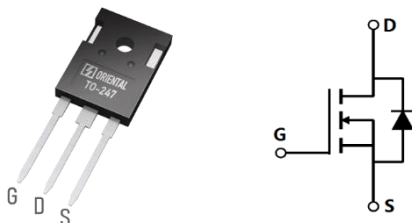
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
I_D , pulse	540	A
$R_{DS(ON)}$, max @ $V_{GS}=10V$	3	$m\Omega$
Q_g	158.8	nC

Marking Information

Product Name	Package	Marking
SFG180N10HF	TO247	SFG180N10H

Package & Pin information



Absolute Maximum Ratings at $T_J=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	180	A
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, \text{pulse}}$	540	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	180	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, \text{pulse}}$	540	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	375	W
Single pulsed avalanche energy ⁴⁾	E_{AS}	1000	mJ
Operation and storage temperature	T_{stg}, T_J	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.33	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient	$R_{\theta JA}$	62	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_J=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		2.5	3.0	$\text{m}\Omega$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}$
Gate resistance	R_G		3.5		Ω	$f=1\text{ MHz}$, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		10953		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		1402		pF	
Reverse transfer capacitance	C_{rss}		33.3		pF	
Turn-on delay time	$t_{d(on)}$		40.7		ns	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $R_G=2.2\ \Omega$, $I_D=25\text{ A}$
Rise time	t_r		31.4		ns	
Turn-off delay time	$t_{d(off)}$		75.4		ns	
Fall time	t_f		16.2		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		158.8		nC	$V_{GS}=10\text{ V}$, $V_{DS}=50\text{ V}$, $I_D=25\text{ A}$
Gate-source charge	Q_{gs}		38.4		nC	
Gate-drain charge	Q_{gd}		41.6		nC	
Gate plateau voltage	$V_{plateau}$		4.6		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		99.2		ns	$V_R=50\text{ V}$, $I_S=25\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		402		nC	
Peak reverse recovery current	I_{rrm}		6.7		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

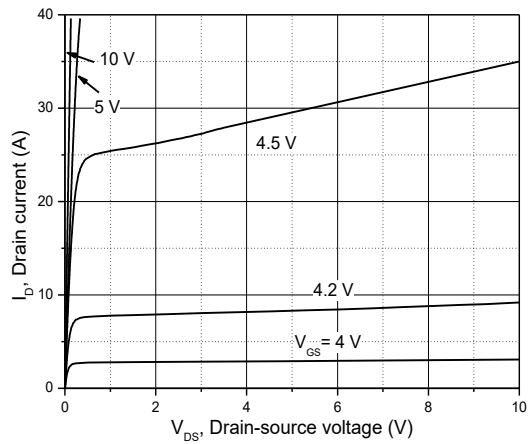


Figure 1. Typ. output characteristics

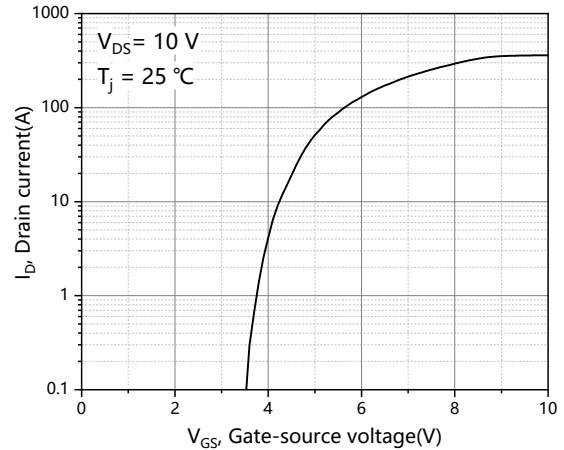


Figure 2. Typ. transfer characteristics

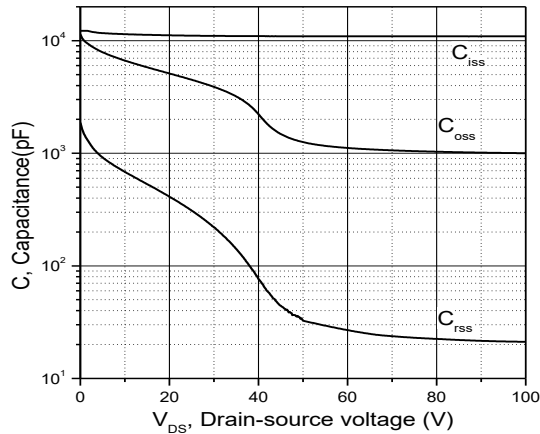


Figure 3. Typ. capacitances

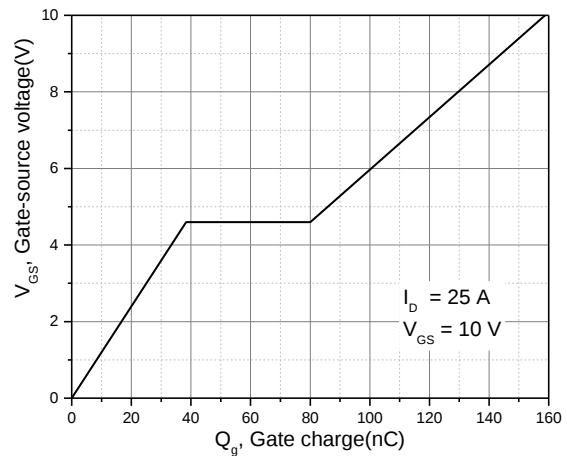


Figure 4. Typ. gate charge

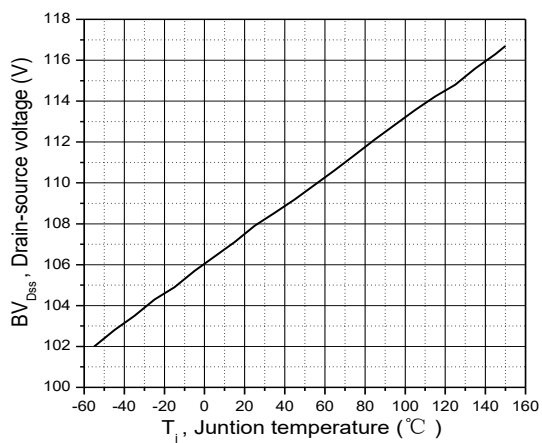


Figure 5. Drain-source breakdown voltage

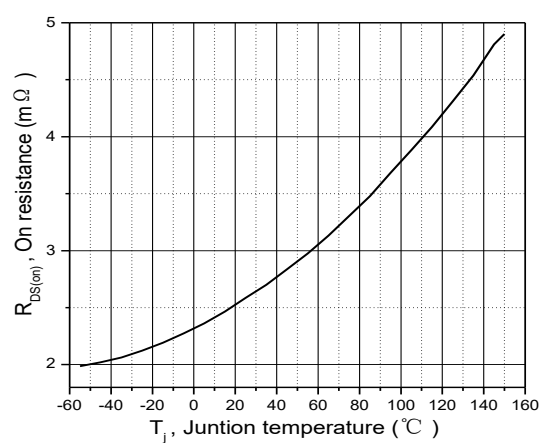


Figure 6. Drain-source on-state resistance

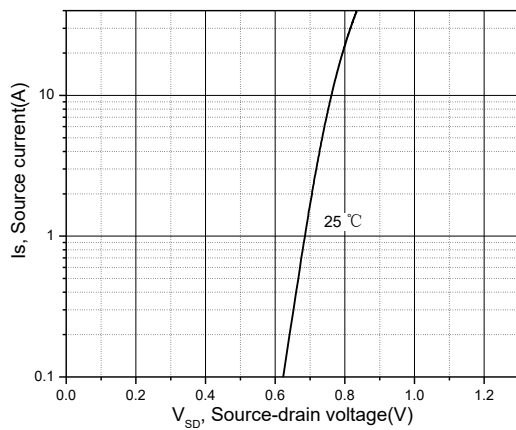


Figure 7. Forward characteristic of body diode

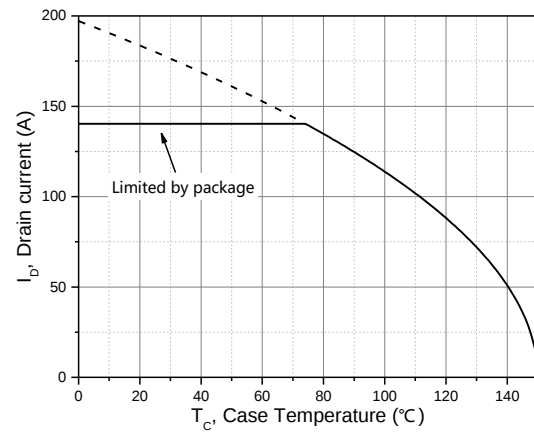


Figure 8. Drain current

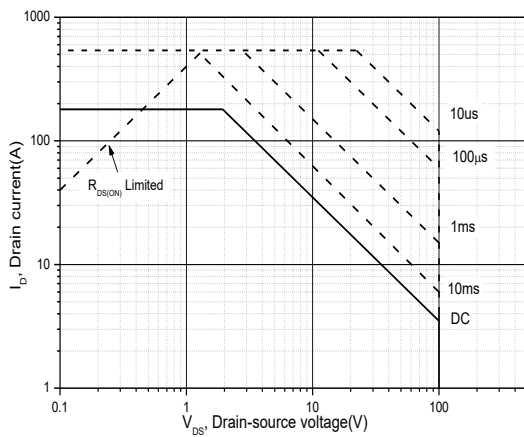


Figure 9. Safe operation area $T_C=25\text{ }^{\circ}\text{C}$

Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

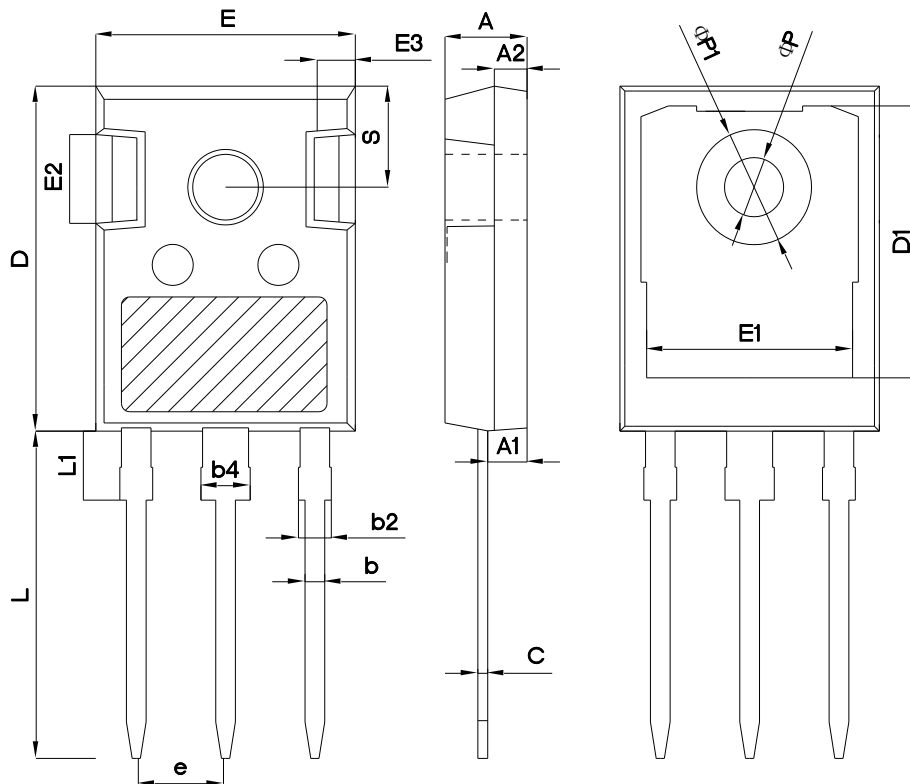


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

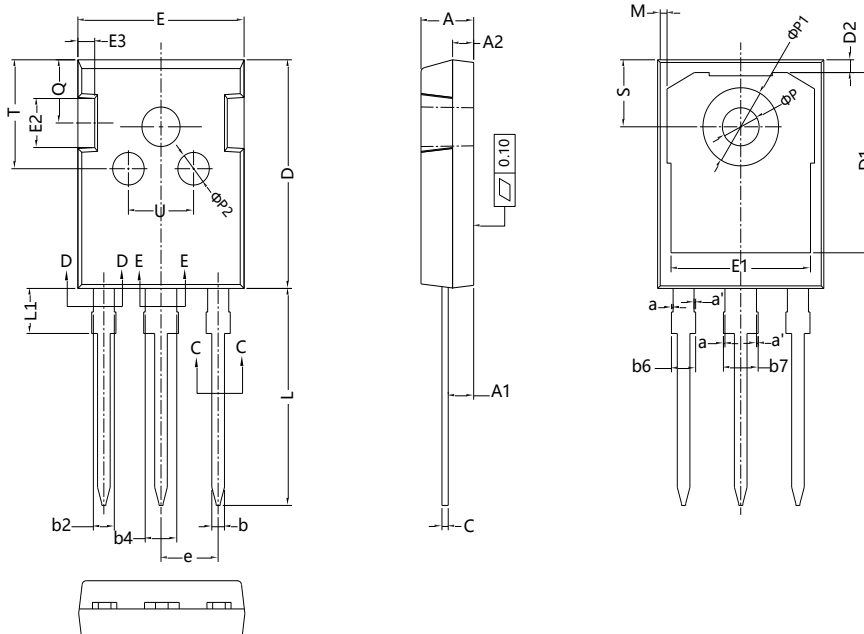
Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15BSC		

Version 1: TO247-P package outline dimension

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0.00	-	0.15
a'	0.00	-	0.15
b	1.16	-	1.26
b2	1.96	-	2.06
b4	2.96	-	3.06
b6	-	-	2.25
b7	-	-	3.25
c	0.59	-	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.40	4.50	4.60
E3	1.50	1.60	1.70
e	5.436 BSC		
L	19.80	19.92	20.10
L1	-	-	4.30
M	0.35	-	0.95
P	3.40	3.50	3.60
P1	7.00	-	7.40
P2	2.40	2.5	2.6
Q	5.60	-	6.0
S	6.05	6.15	6.25
T	9.8	-	10.20
U	6.00	-	6.40

Version 2: TO247-J package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-P	30	11	330	6	1980
TO247-J	30	20	600	4	2400

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG180N10HF	TO247	yes	yes	yes

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